

CMDD6001

**SURFACE MOUNT  
ULTRA LOW LEAKAGE  
SILICON SWITCHING DIODE**



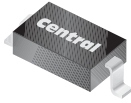
[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMDD6001 type is a silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for switching applications requiring an extremely low leakage diode.

**MARKING CODE: C61**

**SUPERmini™**



**SOD-323 CASE**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
$V_R$	75	V
$V_{RRM}$	100	V
$I_F$	250	mA
$I_{FRM}$	250	mA
$I_{FSM}$	4.0	A
$I_{FSM}$	1.0	A
$P_D$	250	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	500	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_R$	$V_R=75\text{V}$		500	pA
$BV_R$	$I_R=100\mu\text{A}$	100		V
$V_F$	$I_F=1.0\text{mA}$		0.85	V
$V_F$	$I_F=10\text{mA}$		0.95	V
$V_F$	$I_F=100\text{mA}$		1.1	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		3.0	$\mu\text{s}$

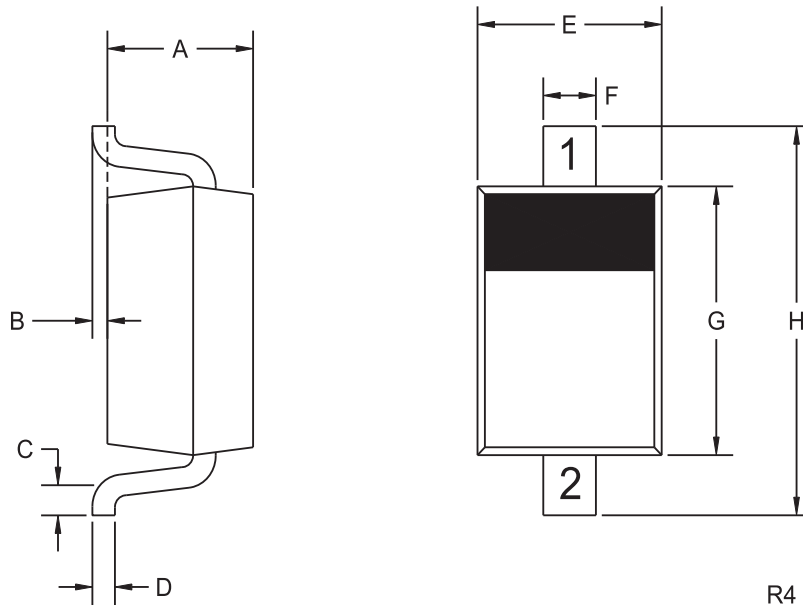
R5 (9-May 2011)

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SOD-323 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: C61

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R5 (9-May 2011)